

Silicon Carbide Power Schottky Diode

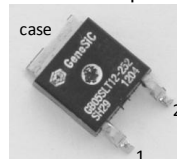
V_{RRM}	=	1200 V
I_F ($T_C = 25^\circ\text{C}$)	=	12 A
I_F ($T_C \leq 150^\circ\text{C}$)	=	5 A
Q_C	=	21 nC

Features

- Industry's leading low leakage currents
- 175 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F

Package

- RoHS Compliant



TO – 252



Advantages

- Low standby power losses
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance
- Low reverse leakage current at operating temperature

Applications

- Power Factor Correction (PFC)
- Switched-Mode Power Supply (SMPS)
- Solar Inverters
- Wind Turbine Inverters
- Motor Drives
- Induction Heating
- Uninterruptible Power Supply (UPS)
- High Voltage Multipliers

Maximum Ratings at $T_J = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	I_F	$T_C = 25^\circ\text{C}$	12	A
Continuous forward current	I_F	$T_C \leq 150^\circ\text{C}$	5	A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 150^\circ\text{C}$	8	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms $T_C = 150^\circ\text{C}$, $t_p = 10$ ms	32 26	A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, $t_p = 10$ μs	120	A
I^2t value	$\int I^2 dt$	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms $T_C = 150^\circ\text{C}$, $t_p = 10$ ms	5 3.4	A ² s
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$	117	W
Operating and storage temperature	T_J , T_{stg}		-55 to 175	$^\circ\text{C}$

Electrical Characteristics at $T_J = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 5$ A, $T_J = 25^\circ\text{C}$ $I_F = 5$ A, $T_J = 175^\circ\text{C}$		1.6 2.6	1.9 3.0	V
Reverse current	I_R	$V_R = 1200$ V, $T_J = 25^\circ\text{C}$ $V_R = 1200$ V, $T_J = 175^\circ\text{C}$		5 10	50 100	μA
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ $dI_F/dt = 200$ A/ μs $T_J = 175^\circ\text{C}$	$V_R = 400$ V		21	nC
			$V_R = 960$ V		35	
Switching time	t_s		$V_R = 400$ V $V_R = 960$ V		< 25	ns
Total capacitance	C	$V_R = 1$ V, $f = 1$ MHz, $T_J = 25^\circ\text{C}$			260	pF
		$V_R = 400$ V, $f = 1$ MHz, $T_J = 25^\circ\text{C}$			25	
		$V_R = 1000$ V, $f = 1$ MHz, $T_J = 25^\circ\text{C}$			20	

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	1.4	$^\circ\text{C/W}$
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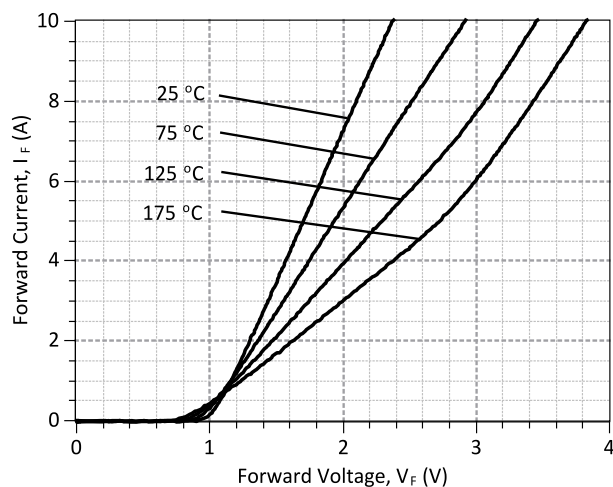


Figure 1: Typical Forward Characteristics

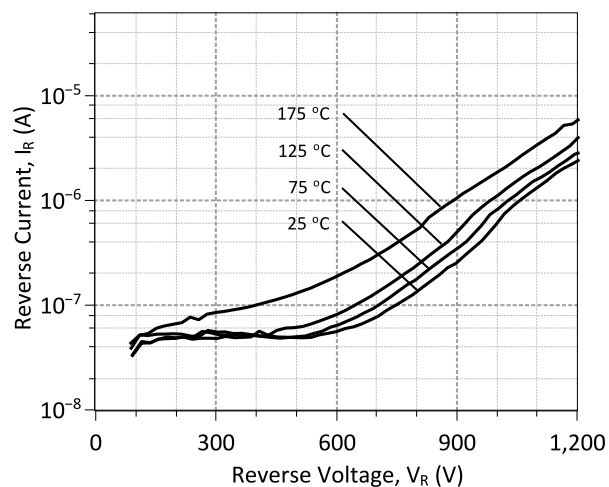


Figure 2: Typical Reverse Characteristics

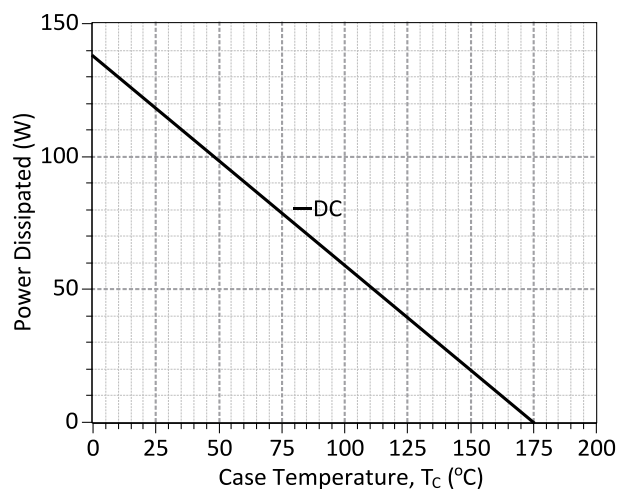
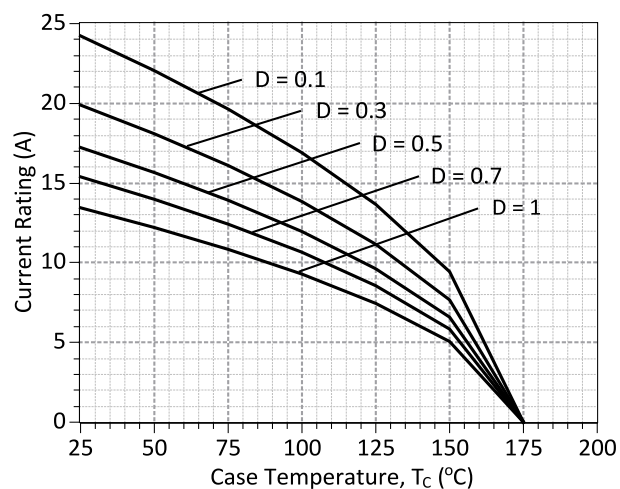


Figure 3: Power Derating Curve



**Figure 4: Current Derating Curves ($D = t_p/T$, $t_p = 400 \mu s$)
(Considering worst case Z_{th} conditions)**

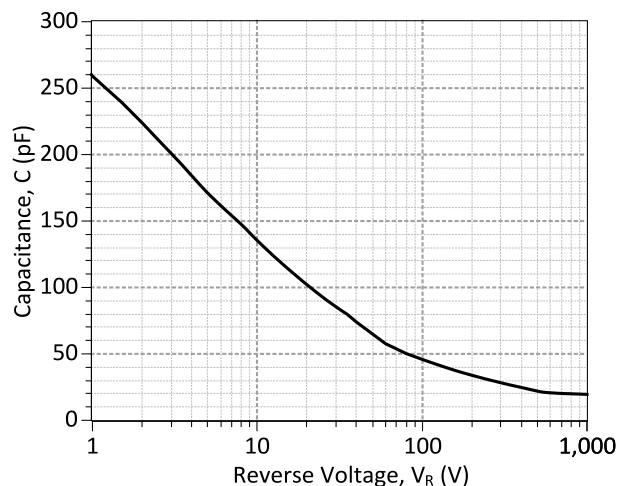


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

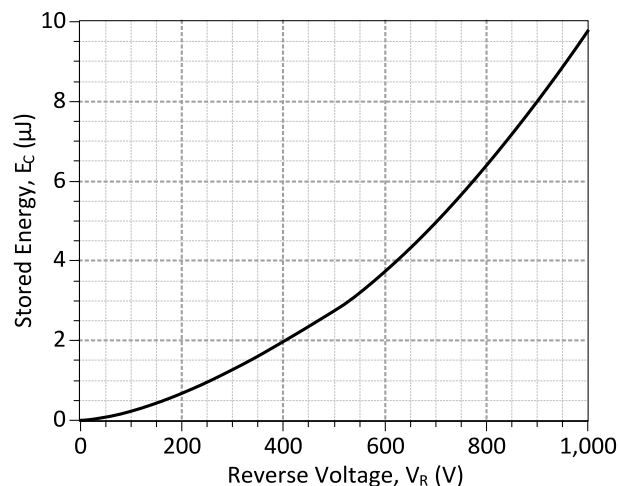


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics

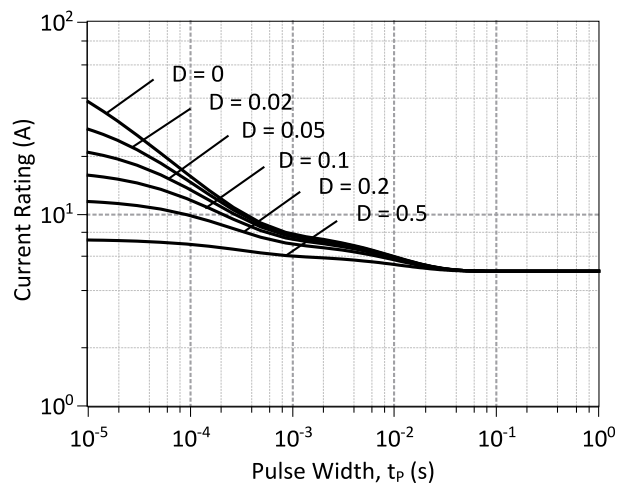


Figure 7: Current vs Pulse Duration Curves at $T_c = 155\text{ }^{\circ}\text{C}$

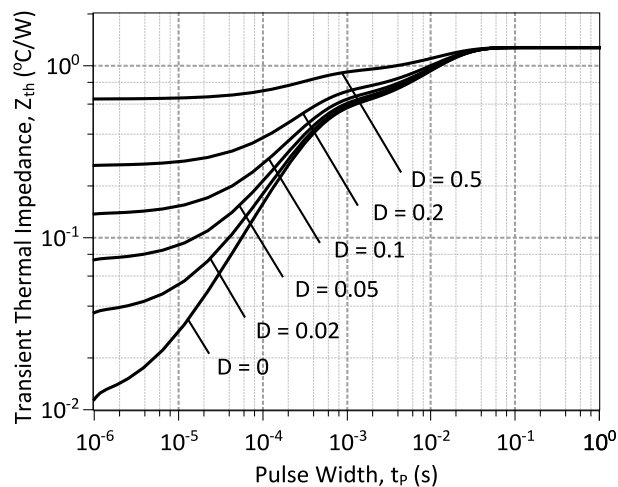
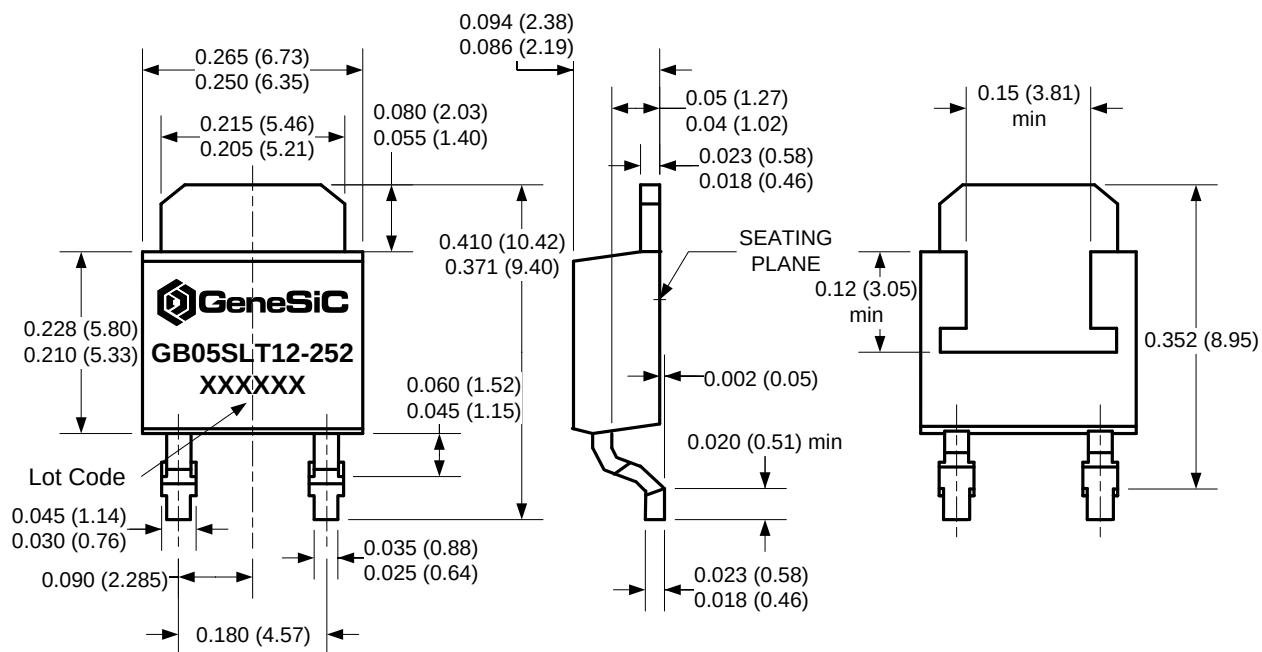


Figure 8: Transient Thermal Impedance

Package Dimensions:

TO-252

PACKAGE OUTLINE



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS
3. CONTROLLED LEAD COPLANARITY <D> 0.004 INCH MAXIMUM

Revision History			
Date	Revision	Comments	Supersedes
2014/08/26	3	Updated Electrical Characteristics	
2013/02/05	2	Second generation update	
2012/05/22	1	Second generation release	
2010/12/14	0	Initial release	

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SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/products_sic/rectifiers/GB05SLT12-252_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GB05SLT12-252.

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*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      04-SEP-2013    $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*      ALL RIGHTS RESERVED
*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB05SLT12-252 SPICE Model
*
.SUBCKT GB05SLT12 ANODE KATHODE
R1 ANODE INT R=((TEMP-24)*0.0015); Temperature Dependant Resistor
D1 INT KATHODE GB05SLT12_25C; Call the 25C Diode Model
D2 ANODE KATHODE GB05SLT12_PIN; Call the PiN Diode Model
.MODEL GB05SLT12_25C D
+ IS      5.83E-18      RS      0.1276
+ N        1           IKF      602
+ EG       1.2          XTI      3
+ CJO      3.00E-10     VJ       0.419
+ M         1.6         FC       0.5
+ TT       1.00E-10     BV       1200
+ IBV      1.00E-03     VPK      1200
+ IAVE      5           TYPE     SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL GB05SLT12_PIN D
+ IS      3.50 E-12     RS      0.3648
+ N        4.409       IKF      73
+ EG       3.23        XTI      -6
+ FC       0.5         TT       0
+ BV       1200        IBV      1.00E-03
+ VPK      1200        IAVE      1
+ TYPE     SiC_PiN
.ENDS
*
*      End of GB05SLT12-252 SPICE Model
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